Elektronische Bauelemente

BCP772

PNP Epitaxial Planar

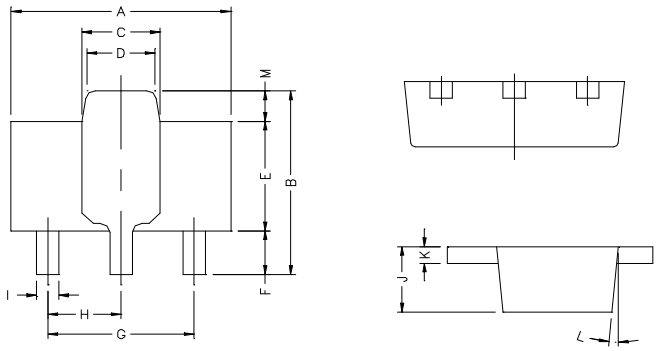
General Purpose Transistor

RoHS Compliant Product

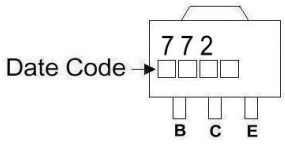
SOT-89

Description

The BCP772 is designed for using in output stage of amplifier, voltage regulator, DC-DC converter and relay driver.



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00 REF.	
B	4.05	4.25	H	1.50 REF.	
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at T_A=25°C (unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collect Current	I_C	-3	A
Total Power Dissipation (TC=25℃)	P_D	1.2	W
Operating Junction and Storage Temperature Range	Tj, Tstg	-55~+150	℃

ELECTRICAL CHARACTERISTICS Tamb=25°C unless otherwise specified

Parameter	Symbol	Min	Typ.	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-40	-	-	V	I_C=-100μA
Collector-Emitter Breakdown Voltage	BV_{CEO}	-30	-	-	V	I_C=-1mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	-	-	V	I_E=-10μA
Collector-Base Cutoff Current	I_{CBO}	-	-	-1	uA	V_{CB}=-30V
Emitter-Base Cutoff Current	I_{EBO}	-	-	-1	uA	V_{BE}=-3V
Collector Saturation Voltage	V_{CE}(sat)	-	-0.3	-0.5	V	I_C=-2A,I_B=-0.2A
Base Satruation Voltage	V_{BE}(sat)	-	-1	-2	V	I_C=-2A,I_B=-0.2A
DC Current Gain	h_{FE}1	30	-	-		V_{CE}=-2V, I_C=-20mA
	h_{FE}2	100	160	500		V_{CE}=-2V, I_C=-1A
Gain-Bandwidth Product	fT	-	80	-	MHz	V_{CE}=-5V, I_C=-20mA,f=100MHz
Output Capacitance	C_{ob}	-	55	-	pF	V_{CB}=-10V, f=1MHz

Classification of hFE2

Rank	Q	P	E
Range	100~200	160~320	250~500

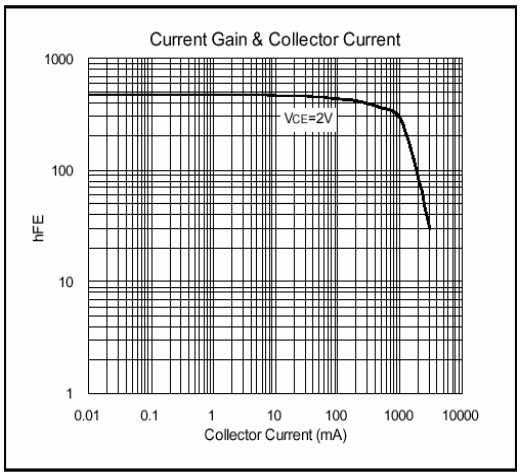
Elektronische Bauelemente

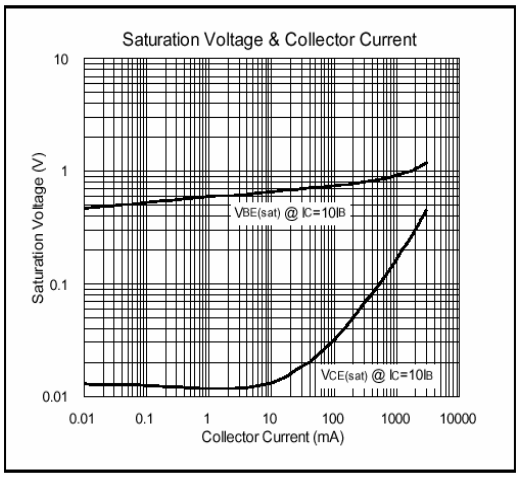
BCP772

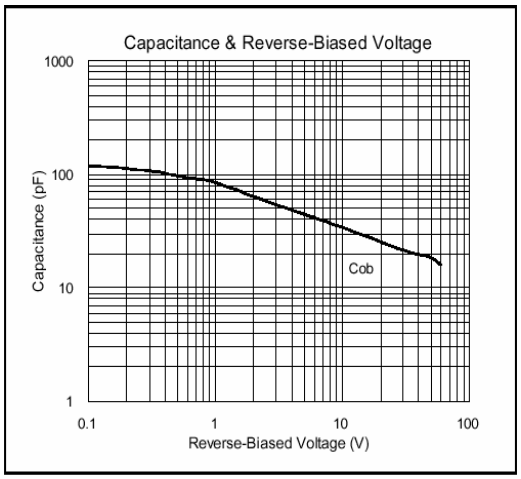
PNP Epitaxial Planar

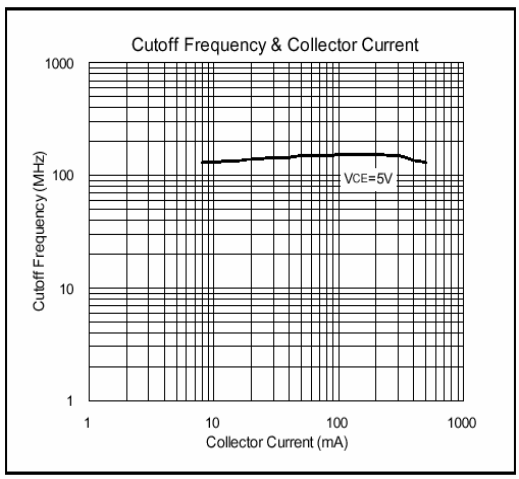
General Purpose Transistor

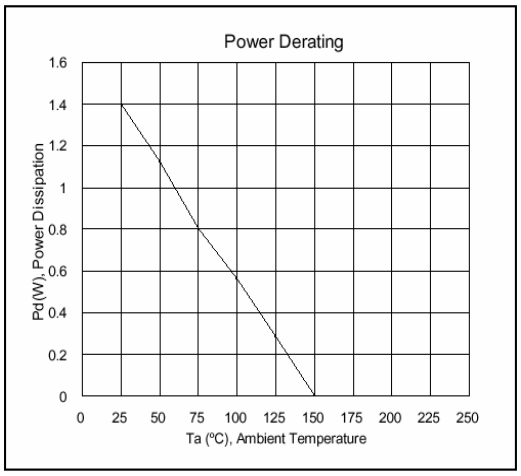
Characteristics Curve

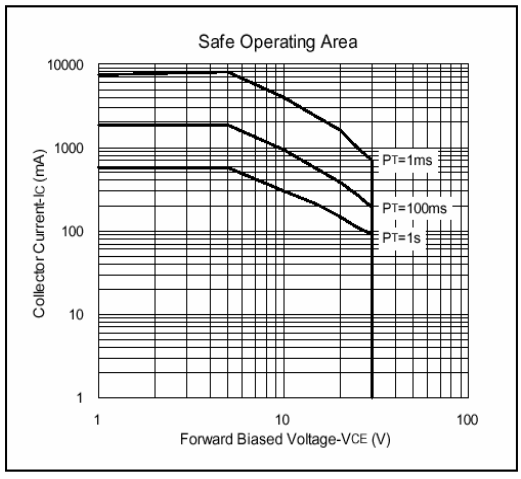












BCP882

NPN Silicon
Epitaxial Planar Transistor

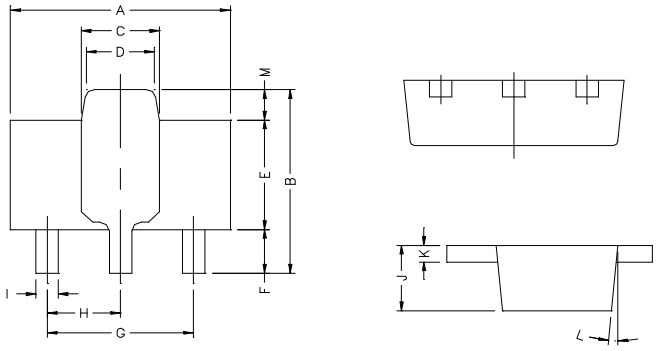
Elektronische Bauelemente

RoHS Compliant Product

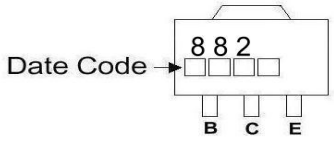
SOT-89

Description

The BCP882 is suited for the output stage of 1.5W audio, voltage regulator, and relay driver.



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00 REF.	
B	4.05	4.25	H	1.50 REF.	
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at T_A=25°C

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	3	A
P_D	Total Power Dissipation	1.2	W
T_J,T_{stg}	Junction and Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS Tamb=25°C unless otherwise specified

Parameter	Symbol	Min	Typ.	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	40	-	-	V	I_C=100μA,I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	30	-	-	V	I_C= 1mA,I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5	-	-	V	I_E= 10μA
Collector-Base Cutoff Current	I_{CBO}	-	-	1	uA	V_{CB}= 30V
Emitter-Base Cutoff Current	I_{EBO}	-	-	1	uA	V_{EB}=3V
Collector Saturation Voltage	V_{CE}(sat)	-	-	0.5	V	I_C=2A,I_B=0.2A
Base-Emitter Saturation Voltage	V_{BE}(sat)	-	-	2	V	I_C=2A,I_B=0.2A
DC Current Gain	h_{FE1}	30	-	-		V_{CE}= 2V, I_C=20mA
	h_{FE2}	100	-	500		V_{CE}= 2V, I_C=1A
Gain-Bandwidth Product	fT	-	90	-	MHz	V_{CE}= 5V, I_C= 0.1A,f=100MHz
Output Capacitance	C_{ob}	-	45	-	pF	V_{CB}=10V, f=1MHz,I_E=0

Classification of hFE

Rank	Q	P	E
Range	100~200	160~320	250~500

Elektronische Bauelemente

BCP882

NPN Silicon
Epitaxial Planar Transistor

Characteristics Curve